

## Amendments to the Claims

Claims 1-10 (Canceled).

11. (Original): Silicon-on-insulator comprising integrated circuitry, comprising:

a substrate comprising a semiconductive silicon comprising layer of silicon-on-insulator circuitry, the silicon comprising layer comprising a pair of source/drain regions formed therein and a channel region formed therein which is received intermediate the source/drain regions;

a transistor gate received operably proximate the channel region; and  
an insulator layer of the silicon-on-insulator circuitry received on the silicon comprising layer, the insulator layer comprising a first silicon dioxide comprising region in contact with the silicon comprising layer and running along at least a portion of the channel region between the source/drain regions, a silicon nitride comprising region in contact with the first silicon dioxide comprising region and running along at least a portion of the channel region, and a second silicon dioxide comprising region in contact with the silicon nitride comprising region, the silicon nitride comprising region being received intermediate the first and second silicon dioxide comprising regions.

12. (Original): The circuitry of claim 11 wherein the silicon nitride comprising region runs along only a portion of the channel region between the source/drain regions.

13. (Original): The circuitry of claim 11 wherein the silicon nitride comprising region runs entirely along the channel region between the source/drain regions.

14. (Original): The circuitry of claim 11 wherein the silicon nitride comprising region has a thickness of from about 10 Angstroms to about 50 Angstroms.

15. (Original): The circuitry of claim 11 wherein the first silicon dioxide comprising region has a thickness of from about 10 Angstroms to about 30 Angstroms.

16. (Original): The circuitry of claim 11 wherein the source/drain regions extend to the insulator layer.

Claim 17-61 (Canceled).